

# CPW4-1200S010B–silicon Carbide Schottky Diode Chip

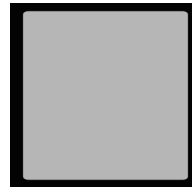
## Z-REC™ RECTIFIER

$V_{RRM} = 1200\text{ V}$   
 $I_{F(AVG)} = 10\text{ A}$   
 $Q_c = 66\text{ nC}$

### Features

- 1200-Volt Schottky Rectifier
- Zero Reverse Recovery
- Zero Forward Recovery
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on  $V_F$

### Chip Outline



Part Number	Anode	Cathode	Package	Marking
CPW4-1200S010B	Al	Ni/Ag	Sawn on Foil	Wafer # on Foil

### Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions	Note
$V_{RRM}$	Repetitive Peak Reverse Voltage	1200	V		
$V_{RSM}$	Surge Peak Reverse Voltage	1300	V		
$V_{DC}$	DC Blocking Voltage	1200	V		
$I_{F(AVG)}$	Average Forward Current	10	A	$T_J=175^\circ\text{C}$	
$I_{FRM}$	Repetitive Peak Forward Surge Current	47	A	$T_C=25^\circ\text{C}$ , $t_p=10\text{ ms}$ , Half Sine Wave	1
$I_{FSM}$	Non-Repetitive Peak Forward Surge Current	71	A	$T_C=25^\circ\text{C}$ , $t_p=10\text{ ms}$ , Half Sine Wave	1
$T_J, T_{stg}$	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$		



## Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$V_F$	Forward Voltage	1.5 2.2	1.8 3	V	$I_F = 10\text{ A}$ $T_J = 25^\circ\text{C}$ $I_F = 10\text{ A}$ $T_J = 175^\circ\text{C}$	
$I_R$	Reverse Current	30 55	250 350	$\mu\text{A}$	$V_R = 1200\text{ V}$ $T_J = 25^\circ\text{C}$ $V_R = 1200\text{ V}$ $T_J = 175^\circ\text{C}$	
$Q_C$	Total Capacitive Charge	66		nC	$V_R = 600\text{ V}$ , $I_F = 2\text{ A}$ $di/dt = 500\text{ A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$	
C	Total Capacitance	754 45 38		pF	$V_R = 0\text{ V}$ , $T_J = 25^\circ\text{C}$ , $f = 1\text{ MHz}$ $V_R = 400\text{ V}$ , $T_J = 25^\circ\text{C}$ , $f = 1\text{ MHz}$ $V_R = 800\text{ V}$ , $T_J = 25^\circ\text{C}$ , $f = 1\text{ MHz}$	

Note:

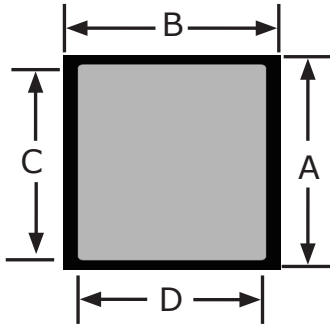
- Assumes  $\theta_{JC}$  Thermal Resistance of  $1.1^\circ\text{C}/\text{W}$  or less

## Mechanical Parameters

Parameter	Typ.	Unit
Die Size	2.26 x 2.26	mm
Anode Pad Size	1.98 x 1.98	mm
Anode Pad Opening	1.70 x 1.70	mm
Thickness	377 $\pm$ 10%	$\mu\text{m}$
Wafer Size	100	mm
Anode Metalization (Al)	4	$\mu\text{m}$
Cathode Metalization (Ni/Ag)	1.4	$\mu\text{m}$
Frontside Passivation	Polyimide	

## Chip Dimensions

---



symbol	dimension	
	mm	inch
A	2.26	0.089
B	2.26	0.089
C	1.70	0.067
D	1.70	0.067

Part Number	Anode	Cathode	Package	Marking
CPW4-1200S010B	Al	Ni/Ag	Sawn on Foil	Wafer # on Foil

The die-on-tape method of delivering these SiC die may be considered a means of temporary storage only. Due to an increase in adhesion over time, die stored for an extended period may affix too strongly to the tape. These die should be stored in a temperature-controlled nitrogen dry box soon after receipt. Cree will further recommend that all die be removed from tape to a waffle pack, to a similar storage medium, or used in production within 2 – 3 weeks of delivery to assure 100% release of all die without issues.

This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, air traffic control systems, or weapons systems.

Copyright © 2011 Cree, Inc. All rights reserved. The information in this document is subject to change without notice. Cree and the Cree logo are registered trademarks and Z-Rec is a trademark of Cree, Inc.

Cree, Inc.  
 4600 Silicon Drive  
 Durham, NC 27703  
 USA Tel: +1.919.313.5300  
 Fax: +1.919.313.5451  
[www.cree.com/power](http://www.cree.com/power)